

Dual N-channel TrenchMOS logic level FET

Rev. 04 — 27 April 2010

Product data sheet

1. Product profile

1.1 General description

Dual logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

Low conduction losses due to low on-state resistance

1.3 Applications

- Battery chargers
- DC-to-DC convertors

1.4 Quick reference data

- Suitable for logic level gate drive sources
- Notebook computers
- Portable equipment

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	20	V
I _D	drain current	$T_{sp} = 25 \text{ °C}$; Single device conducting; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	10.9	A
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	4.17	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 2.5 V; I_D = 3 A; T_j = 25 °C	-	25	35	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 6 \text{ A}; V_{DS} = 16 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{1}$	-	6	-	nC



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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	SOT96-1 (SO8)	S1 G1 S2 G2
7	D1	drain1		mbk725
8	D1	drain1		

3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PHKD6N02LT	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1	

4. Limiting values

Table 4. Limiting values

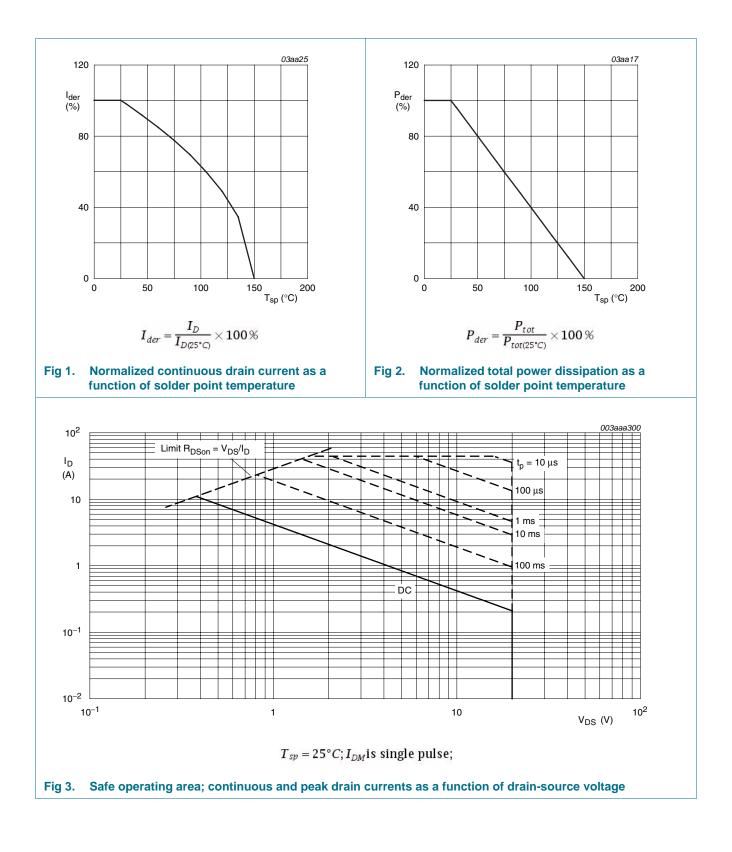
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	20	V
V _{DGR}	drain-gate voltage	$T_j \le 150 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	-	20	V
V _{GS}	gate-source voltage		-12	-	12	V
I _D	drain current	T _{sp} = 100 °C; Single device conducting; see <u>Figure 1</u>	-	-	6.8	A
		$T_{sp} = 25 \text{ °C}$; Single device conducting; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	10.9	А
I _{DM}	peak drain current	$T_{sp} = 25 \text{ °C}; t_p \le 100 \mu\text{s}; \text{ pulsed}; \text{ Single}$ device conducting; see <u>Figure 3</u>	-	-	44	А
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	4.17	W
T _{stg}	storage temperature		-55	-	150	°C
Tj	junction temperature		-55	-	150	°C
Source-drain	diode					
ls	source current	T _{sp} = 25 °C	-	-	3.5	А
I _{SM}	peak source current	$T_{sp} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed}$	-	-	44	А

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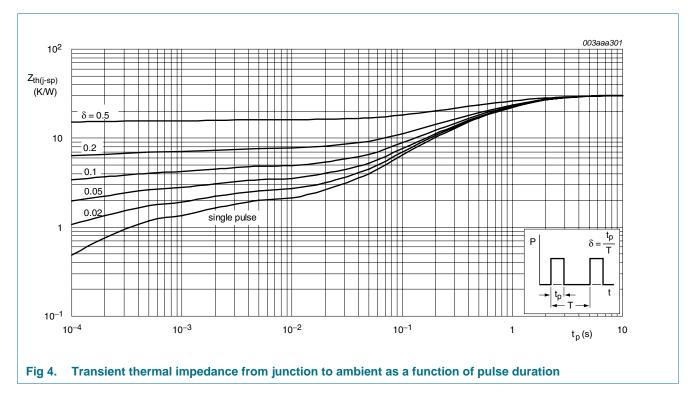
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	see Figure 4	-	-	30	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on printed-circuit board	-	70	-	K/W



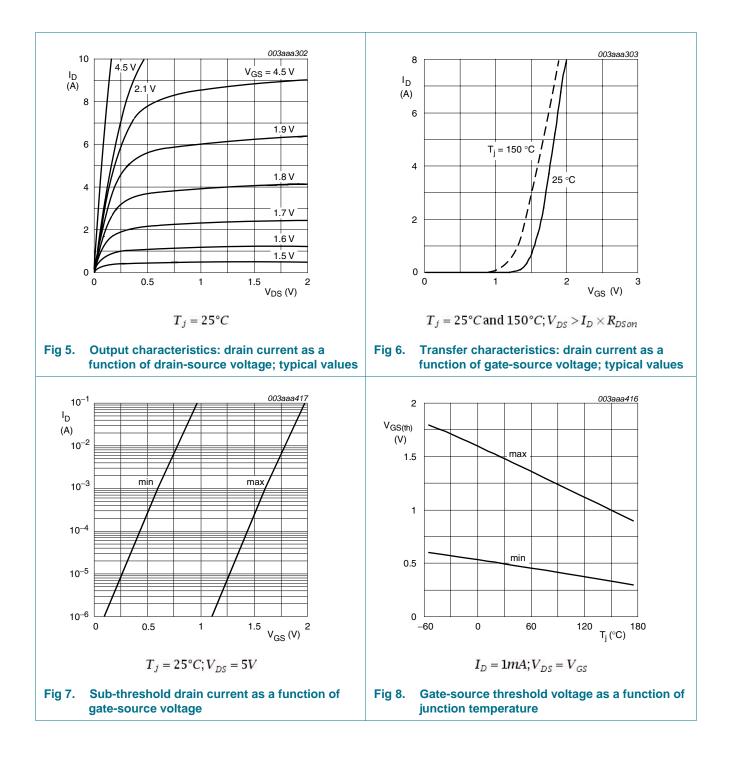
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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	20	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = 10 V; T _j = 25 °C; see <u>Figure 8</u>	0.5	-	1.5	V
I _{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon} drain-source resistance	drain-source on-state	V_{GS} = 2.5 V; I_D = 3 A; T_j = 25 °C	-	25	35	mΩ
	resistance	V _{GS} = 5 V; I _D = 3 A; T _j = 150 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	-	35	mΩ
		V _{GS} = 5 V; I _D = 3 A; T _j = 25 °C; see <u>Figure 9;</u> see <u>Figure 10</u>	-	16	20	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 6 \text{ A}; V_{DS} = 16 \text{ V}; V_{GS} = 5 \text{ V}; T_j = 25 \text{ °C};$	-	15.3	-	nC
Q _{GS}	gate-source charge	see <u>Figure 11</u>	-	2.2	-	nC
Q_{GD}	gate-drain charge		-	6	-	nC
C _{iss}	input capacitance	$V_{DS} = 10 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C};$	-	950	-	pF
C _{oss}	output capacitance	see <u>Figure 12</u>	-	355	-	pF
C _{rss}	reverse transfer capacitance		-	256	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; R_{L} = 3.3 Ω; V_{GS} = 5 V;	-	15	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	49	-	ns
t _{d(off)}	turn-off delay time		-	50	-	ns
t _f	fall time		-	23	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_S = 6 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{100000000000000000000000000000000000$	-	-	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 6 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	40	-	ns
Q _r	recovered charge	V _{DS} = 20 V; T _j = 25 °C	-	7	-	nC

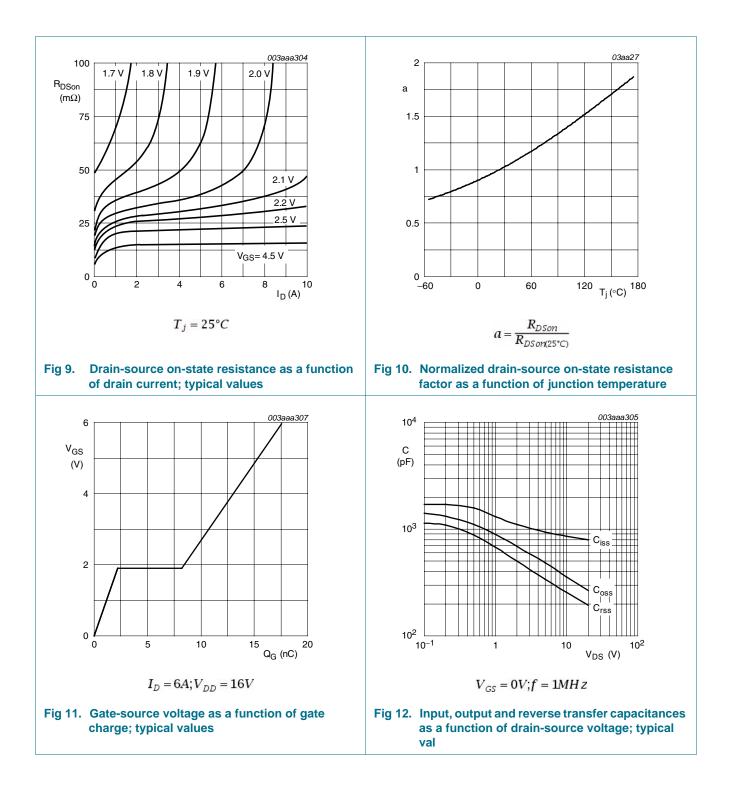
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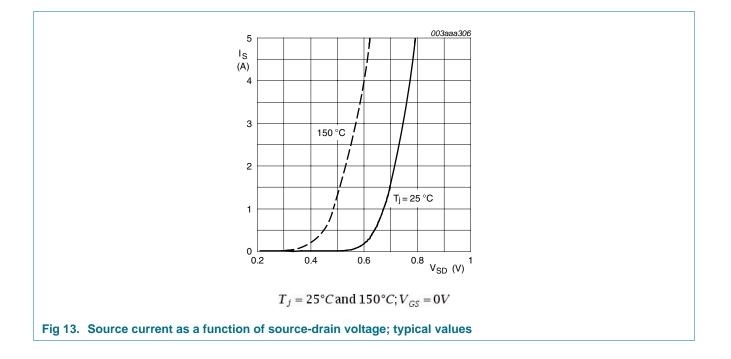


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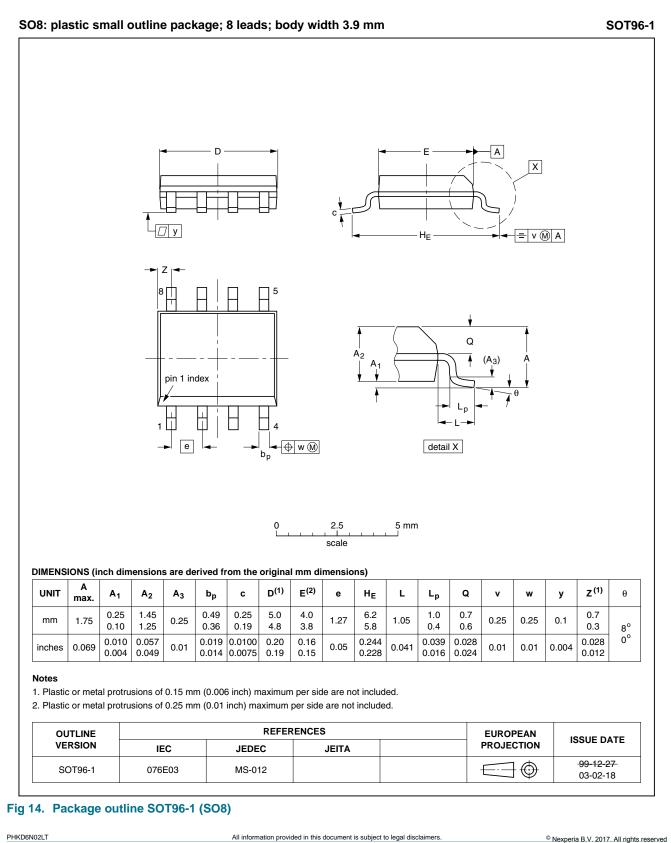
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7. Package outline



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8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHKD6N02LT_4	20100427	Product data sheet	-	PHKD6N02LT_3
Modifications:	 Various cha 	anges to content.		
PHKD6N02LT_3	20091119	Product data sheet	-	PHKD6N02LT-02
PHKD6N02LT-02	20030812	Product data	-	PHKD6N02LT-01
PHKD6N02LT-01	20010907	Product data	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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